## **CMLM0705**

## **MULTI DISCRETE MODULE**™

SURFACE MOUNT SILICON PNP SWITCHING TRANSISTOR AND LOW  $V_F$  SCHOTTKY DIODE



SOT-563 CASE



www.centralsemi.com

## **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLM0705 is a Multi Discrete Module™ consisting of a single PNP transistor and a Schottky diode packaged in a space saving SOT-563 case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

- Combination: Small Signal Switching PNP Transistor and Low V<sub>F</sub> Schottky Diode.
- Complementary Device: CMLM2205

#### **MARKING CODE: C75**

| MAXIMUM RATINGS - CASE: (T <sub>A</sub> =25°C) | SYMBOL                            |             | UNITS |
|------------------------------------------------|-----------------------------------|-------------|-------|
| Power Dissipation                              | $P_{D}$                           | 350         | mW    |
| Operating and Storage Junction Temperature     | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150 | °C    |
| Thermal Resistance                             | $\Theta_{\sf JA}$                 | 357         | °C/W  |
| MAXIMUM RATINGS - Q1: (T <sub>A</sub> =25°C)   | SYMBOL                            |             | UNITS |
| Collector-Base Voltage                         | $V_{CBO}$                         | 90          | V     |
| Collector-Emitter Voltage                      | VCEO                              | 60          | V     |
| Emitter-Base Voltage                           | VEBO                              | 6.0         | V     |
| Continuous Collector Current                   | IC                                | 600         | mA    |
| MAXIMUM RATINGS - D1: (T <sub>A</sub> =25°C)   | SYMBOL                            |             | UNITS |
| Peak Repetitive Reverse Voltage                | $V_{RRM}$                         | 40          | V     |
| Continuous Forward Current                     | I <sub>F</sub>                    | 500         | mA    |
| Peak Repetitive Forward Current, tp≤1.0ms      | I <sub>FRM</sub>                  | 3.5         | Α     |
| Peak Forward Surge Current, tp=8.0ms           | IFSM                              | 10          | Α     |

| FI FCTRICAL | CHARACTERISTICS | - O1· | $(T_{\Lambda}=25^{\circ}C$ | unless | otherwise noted | ١ |
|-------------|-----------------|-------|----------------------------|--------|-----------------|---|

| SYMBOL               | TEST CONDITIONS                             | MIN | TYP   | MAX | UNITS |
|----------------------|---------------------------------------------|-----|-------|-----|-------|
| I <sub>CBO</sub>     | V <sub>CB</sub> =50V                        |     |       | 10  | nA    |
| I <sub>CBO</sub>     | V <sub>CB</sub> =50V, T <sub>A</sub> =125°C |     |       | 10  | μΑ    |
| I <sub>CEV</sub>     | $V_{CE}$ =30V, $V_{BE}$ =0.5V               |     |       | 50  | nA    |
| BV <sub>CBO</sub>    | I <sub>C</sub> =10μA                        | 90  | 115   |     | V     |
| <b>BV</b> CEO        | I <sub>C</sub> =10mA                        | 60  |       |     | V     |
| BV <sub>EBO</sub>    | I <sub>E</sub> =10μA                        | 5.0 |       |     | V     |
| V <sub>CE(SAT)</sub> | $I_C$ =150mA, $I_B$ =15mA                   |     | 0.113 | 0.2 | V     |
| V <sub>CE(SAT)</sub> | $I_C$ =500mA, $I_B$ =50mA                   |     | 0.280 | 0.7 | V     |
| V <sub>BE(SAT)</sub> | $I_C$ =150mA, $I_B$ =15mA                   |     |       | 1.3 | V     |
| V <sub>BE(SAT)</sub> | $I_C$ =500mA, $I_B$ =50mA                   |     |       | 2.6 | V     |
| h <sub>FE</sub>      | $V_{CE}$ =10V, $I_{C}$ =0.1mA               | 100 | 205   |     |       |
| h <sub>FE</sub>      | $V_{CE}$ =10V, $I_{C}$ =1.0mA               | 100 |       |     |       |
| h <sub>FE</sub>      | $V_{CE}$ =10V, $I_{C}$ =10mA                | 100 |       |     |       |
| h <sub>FE</sub>      | $V_{CE}$ =10V, $I_{C}$ =150mA               | 100 |       | 300 |       |
| h <sub>FE</sub>      | V <sub>CE</sub> =10V, I <sub>C</sub> =500mA | 75  | 110   |     |       |

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# **MULTI DISCRETE MODULE**™

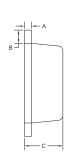
**SURFACE MOUNT SILICON** PNP SWITCHING TRANSISTOR AND LOW  $V_F$  SCHOTTKY DIODE

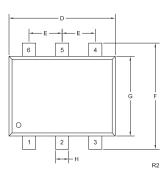


| ELECTRIC | AL CHARACTERISTICS - Q1 - Continued: |
|----------|--------------------------------------|
| SVMBOL   | TEST CONDITIONS                      |

| SYMBOL          | TEST CONDITIONS                                               | MIN | MAX  | UNITS |
|-----------------|---------------------------------------------------------------|-----|------|-------|
| $f_{T}$         | $V_{CE}$ =20V, $I_{C}$ =50mA, f=100MHz                        | 200 |      | MHz   |
| $C_{ob}$        | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1.0MHz             |     | 8.0  | pF    |
| C <sub>ib</sub> | $V_{BE}$ =2.0V, $I_{C}$ =0, f=1.0MHz                          |     | 30   | pF    |
| t <sub>on</sub> | $V_{CC}$ =30V, $V_{BE}$ =0.5V, $I_{C}$ =150mA, $I_{B1}$ =15mA |     | 45   | ns    |
| $t_{d}$         | $V_{CC}$ =30V, $V_{BE}$ =0.5V, $I_{C}$ =150mA, $I_{B1}$ =15mA |     | 10   | ns    |
| t <sub>r</sub>  | $V_{CC}$ =30V, $V_{BE}$ =0.5V, $I_{C}$ =150mA, $I_{B1}$ =15mA |     | 40   | ns    |
| toff            | $V_{CC}$ =6.0V, $I_{C}$ =150mA, $I_{B1}$ = $I_{B2}$ =15mA     |     | 100  | ns    |
| $t_{s}$         | $V_{CC}$ =6.0V, $I_{C}$ =150mA, $I_{B1}$ = $I_{B2}$ =15mA     |     | 80   | ns    |
| t <sub>f</sub>  | $V_{CC}$ =6.0V, $I_{C}$ =150mA, $I_{B1}$ = $I_{B2}$ =15mA     |     | 30   | ns    |
| ELECTRIC        | CAL CHARACTERISTICS - D1: (T <sub>A</sub> =25°C)              |     |      |       |
| $I_{R}$         | V <sub>R</sub> =10V                                           |     | 20   | μA    |
| $I_{R}$         | V <sub>R</sub> =30V                                           |     | 100  | μA    |
| $BV_R$          | I <sub>R</sub> =500μA                                         | 40  |      | V     |
| $V_{F}$         | I <sub>F</sub> =100μA                                         |     | 0.13 | V     |
| ٧F              | I <sub>F</sub> =1.0mA                                         |     | 0.21 | V     |
| $V_{F}$         | I <sub>F</sub> =10mA                                          |     | 0.27 | V     |
| $V_{F}$         | I <sub>F</sub> =100mA                                         |     | 0.35 | V     |
| $V_{F}$         | I <sub>F</sub> =500mA                                         |     | 0.47 | V     |
| $C_{J}$         | V <sub>R</sub> =1.0V, f=1.0MHz                                |     | 50   | pF    |

## **SOT-563 CASE - MECHANICAL OUTLINE**





| 6  | 5 4  |
|----|------|
|    |      |
| Q1 | D1 ¥ |
| 1  | 2 3  |

| DIMENSIONS        |        |       |        |       |  |
|-------------------|--------|-------|--------|-------|--|
|                   | INCHES |       | MILLIM | ETERS |  |
| SYMBOL            | MIN    | MAX   | MIN    | MAX   |  |
| Α                 | 0.0027 | 0.007 | 0.07   | 0.18  |  |
| В                 | 0.008  |       | 0.20   |       |  |
| С                 | 0.017  | 0.024 | 0.45   | 0.60  |  |
| D                 | 0.059  | 0.067 | 1.50   | 1.70  |  |
| E                 | 0.020  |       | 0.50   |       |  |
| F                 | 0.059  | 0.067 | 1.50   | 1.70  |  |
| G                 | 0.043  | 0.051 | 1.10   | 1.30  |  |
| Н                 | 0.006  | 0.012 | 0.15   | 0.30  |  |
| SOT-563 (REV: R2) |        |       |        |       |  |

- LEAD CODE: 1) Emitter Q1
- 2) Base Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Collector Q1

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R3 (1-July 2015)

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#### **SERVICES**

- · Bonded Inventory
- · Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/Multi Discrete Modules (MDM™)
- · Bare Die Available for Hybrid Applications

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R3 (1-July 2015)